# Jeffrey H Warner

List of Publications by Year
in descending order



| 36 | 465 | 567281 15 | 752698 20 |
|---|---|---|---|
| papers | citations | h-index | g-index |

| 36 | 36 | 36 | 260 |
|---|---|---|---|
| all docs | docs citations | times ranked | citing authors |

| # | Article | IF | Citations |
|---|---|---|---|
| 1 | Design of Radiation-Hardened RF Low-Noise Amplifiers Using Inverse-Mode SiGe HBTs. IEEE Transactions on Nuclear Science, 2014, 61, 3218-3225. | 2.0 | 34 |
| 2 | A Dosimetry Methodology for Two-Photon Absorption Induced Single-Event Effects Measurements. IEEE Transactions on Nuclear Science, 2014, 61, 3416-3423. | 2.0 | 30 |
| 3 | Correlation of Telemetered Solar Array Data With Particle Detector Data On GPS Spacecraft. IEEE Transactions on Nuclear Science, 2011, 58, 3118-3125. | 2.0 | 27 |
| 4 | Experimental Validation of an Equivalent LET Approach for Correlating Heavy-Ion and Laser-Induced Charge Deposition. IEEE Transactions on Nuclear Science, 2018, 65, 1724-1733. | 2.0 | 25 |
| 5 | Using TCAD Modeling to Compare Heavy-Ion and Laser-Induced Single Event Transients in SiGe HBTs. IEEE Transactions on Nuclear Science, 2017, 64, 398-405. | 2.0 | 24 |
| 6 | The Impact of Technology Scaling on the Single-Event Transient Response of SiGe HBTs. IEEE Transactions on Nuclear Science, 2017, 64, 406-414. | 2.0 | 22 |
| 7 | An Investigation of Single-Event Effects and Potential SEU Mitigation Strategies in Fourth-Generation, 90Ânm SiGe BiCMOS. IEEE Transactions on Nuclear Science, 2013, 60, 4175-4183. | 2.0 | 20 |
| 8 | Two-Photon Absorption Induced Single-Event Effects: Correlation Between Experiment and Simulation. IEEE Transactions on Nuclear Science, 2015, 62, 2867-2873. | 2.0 | 18 |
| 9 | Simulation of Laser-Based Two-Photon Absorption Induced Charge Carrier Generation in Silicon. IEEE Transactions on Nuclear Science, 2015, 62, 1550-1557. | 2.0 | 18 |
| 10 | A Simplified Approach for Predicting Pulsed-Laser-Induced Carrier Generation in Semiconductor. IEEE Transactions on Nuclear Science, 2017, 64, 1006-1013. | 2.0 | 18 |
| 11 | An Investigation of Single-Event Effect Modeling Techniques for a SiGe RF Low-Noise Amplifier. IEEE Transactions on Nuclear Science, 2016, 63, 273-280. | 2.0 | 16 |
| 12 | New Approach for Pulsed-Laser Testing That Mimics Heavy-Ion Charge Deposition Profiles. IEEE Transactions on Nuclear Science, 2020, 67, 81-90. | 2.0 | 16 |
| 13 | Simulation of Light-Matter Interaction and Two-Photon Absorption Induced Charge Deposition by Ultrashort Optical Pulses in Silicon. IEEE Transactions on Nuclear Science, 2014, 61, 3504-3511. | 2.0 | 15 |
| 14 | On the Transient Response of a Complementary (npn <formula formulatype="inline"><tex) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 Transactions on Nuclear Science, 2014, 61, 3146-3153. | 2.0 | 15 |
| 15 | Optimizing Optical Parameters to Facilitate Correlation of Laser- and Heavy-Ion-Induced Single-Event Transients in SiGe HBTs. IEEE Transactions on Nuclear Science, 2019, 66, 359-367. | 2.0 | 15 |
| 16 | Strong Correlation Between Experiment and Simulation for Two-Photon Absorption Induced Carrier Generation. IEEE Transactions on Nuclear Science, 2017, 64, 1133-1136. | 2.0 | 14 |
| 17 | Single-Event Upsets in Substrate-Etched CMOS SOI SRAMs Using Ultraviolet Optical Pulses With Sub-Micrometer Spot Size. IEEE Transactions on Nuclear Science, 2013, 60, 4184-4191. | 2.0 | 13 |
| 18 | RHBD Technique for Single-Event Charge Cancellation in Folded-Cascode Amplifiers. IEEE Transactions on Nuclear Science, 2013, 60, 2756-2761. | 2.0 | 12 |

| # | Article | IF | Citations |
|---|---|---|---|
| 19 | Evaluating the Effects of Single Event Transients in FET-Based Single-Pole Double-Throw RF Switches. IEEE Transactions on Nuclear Science, 2014, 61, 756-765. | 2.0 | 12 |
| 20 | Single-Event Effects in a W-Band (75-110ÂGHz) Radar Down-Conversion Mixer Implemented in 90Ânm, 300ÂGHz SiGe HBT Technology. IEEE Transactions on Nuclear Science, 2015, 62, 2657-2665. | 2.0 | 12 |
| 21 | Evaluating the Influence of Various Body-Contacting Schemes on Single Event Transients in 45-nm SOI CMOS. IEEE Transactions on Nuclear Science, 2010, , . | 2.0 | 10 |
| 22 | Comparison of Single and Two-Photon Absorption for Laser Characterization of Single-Event Upsets in SOI SRAMs. IEEE Transactions on Nuclear Science, 2011, 58, 2968-2975. | 2.0 | 10 |
| 23 | SiGe HBT Profiles With Enhanced Inverse-Mode Operation and Their Impact on Single-Event Transients. IEEE Transactions on Nuclear Science, 2018, 65, 399-406. | 2.0 | 9 |
| 24 | Using Bessel beams and two-photon absorption to predict radiation effects in microelectronics. Optics Express, 2019, 27, 37652. | 3.4 | 9 |
| 25 | Single-Event Transient Response of Comparator Pre-Amplifiers in a Complementary SiGe Technology. IEEE Transactions on Nuclear Science, 2017, 64, 89-96. | 2.0 | 8 |
| 26 | Utilizing SiGe HBT Power Detectors for Sensing Single-Event Transients in RF Circuits. IEEE Transactions on Nuclear Science, 2018, 65, 239-248. | 2.0 | 8 |
| 27 | Comparison of Single-Event Transients in SiGe HBTs on Bulk and Thick-Film SOI. IEEE Transactions on Nuclear Science, 2020, 67, 71-80. | 2.0 | 7 |
| 28 | Single-Event Effects in High-Frequency Linear Amplifiers: Experiment and Analysis. IEEE Transactions on Nuclear Science, 2017, 64, 125-132. | 2.0 | 5 |
| 29 | Single-Event Effects in a Millimeter-Wave Receiver Front-End Implemented in 90 nm, 300 GHz SiGe HBT Technology. IEEE Transactions on Nuclear Science, 2017, 64, 536-543. | 2.0 | 5 |
| 30 | The Role of Negative Feedback Effects on Single-Event Transients in SiGe HBT Analog Circuits. IEEE Transactions on Nuclear Science, 2015, 62, 2599-2605. | 2.0 | 4 |
| 31 | Single Event Measurement and Analysis of Antimony Based n-Channel Quantum-Well MOSFET With High-<formula formulatype="inline"><tex Notation="TeX">$kappa$</tex> </formula> Dielectric. IEEE Transactions on Nuclear Science, 2015, 62, 2807-2814. | 2.0 | 3 |
| 32 | A Low-Power, Real-Time Displacement Damage Dosimeter. IEEE Transactions on Nuclear Science, 2019, 66, 290-298. | 2.0 | 3 |
| 33 | Best Practices for Using Electrostatic Discharge Protection Techniques for Single-Event Transient Mitigation. IEEE Transactions on Nuclear Science, 2019, 66, 240-247. | 2.0 | 3 |
| 34 | Tradeoffs Between RF Performance and SET Robustness in Low-Noise Amplifiers in a Complementary SiGe BiCMOS Platform. IEEE Transactions on Nuclear Science, 2020, 67, 1521-1529. | 2.0 | 3 |
| 35 | Single-Event Measurement and Analysis of Antimony-Based p-Channel Quantum-Well MOSFETs With High- $kappa $ Dielectric. IEEE Transactions on Nuclear Science, 2017, 64, 434-440. | 2.0 | 1 |
| 36 | The Effects of Temperature on the Single-Event Transient Response of a High-Voltage (>30 V) Complementary SiGe-on-SOI Technology. IEEE Transactions on Nuclear Science, 2019, 66, 389-396. | 2.0 | 1 |